

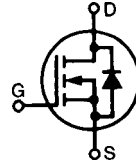
HiPerFET™ Power MOSFETs Q-Class

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low Q_g

IXFH 80N20Q
IXFK 80N20Q
IXFT 80N20Q

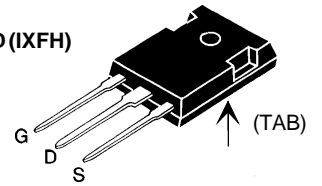
V_{DSS} = 200 V
I_{D25} = 80 A
R_{DS(on)} = 28 mΩ
t_{rr} ≤ 200 ns

Preliminary data sheet

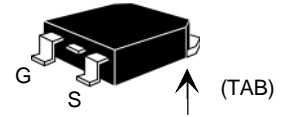


| Symbol | Test Conditions | Maximum Ratings | |
|------------------|---|------------------|--------------------------------------|
| V _{DSS} | T _J = 25°C to 150°C | 200 | V |
| V _{DGR} | T _J = 25°C to 150°C; R _{GS} = 1 MΩ | 200 | V |
| V _{GS} | Continuous | ±20 | V |
| V _{GSM} | Transient | ±30 | V |
| I _{D25} | T _C = 25°C | 80 | A |
| I _{DM} | T _C = 25°C, pulse width limited by T _{JM} | 320 | A |
| I _{AR} | T _C = 25°C | 80 | A |
| E _{AR} | T _C = 25°C | 45 | mJ |
| E _{AS} | T _C = 25°C | 1.5 | J |
| dv/dt | I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω | 5 | V/ns |
| P _D | T _C = 25°C | 360 | W |
| T _J | | -55 ... +150 | °C |
| T _{JM} | | 150 | °C |
| T _{stg} | | -55 ... +150 | °C |
| T _L | 1.6 mm (0.063 in) from case for 10 s | 300 | °C |
| M _d | Mounting torque | TO-247 TO-264 | 1.13/10 Nm/lb.in. 0.9/6 Nm/lb.in. |
| Weight | | TO-247 | 6 g |
| | | TO-264 | 10 g |
| | | TO-268 | 4 g |

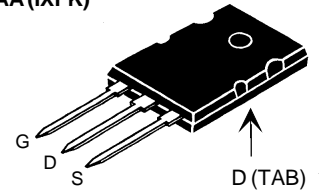
TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



TO-264 AA (IXFK)



G = Gate
S = Source

TAB = Drain

| Symbol | Test Conditions | Characteristic Values (T _J = 25°C, unless otherwise specified) | | |
|---------------------|---|--|------|---------|
| | | min. | typ. | max. |
| V _{DSS} | V _{GS} = 0 V, I _D = 250 μA | 200 | | V |
| V _{GS(th)} | V _{DS} = V _{GS} , I _D = 4 mA | 2.0 | | 4.0 V |
| I _{GSS} | V _{GS} = ±20 V _{DC} , V _{DS} = 0 | | | ±100 nA |
| I _{DSS} | V _{DS} = V _{DSS} V _{GS} = 0 V | T _J = 25°C | | 25 μA |
| | | T _J = 125°C | | 1 mA |
| R _{DS(on)} | V _{GS} = 10 V, I _D = 0.5 • I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 % | | | 28 mΩ |

Features

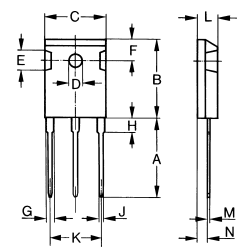
- Low gate charge
- International standard packages
- Epoxy meet UL94V-0, flammability classification
- Low R_{DS(on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

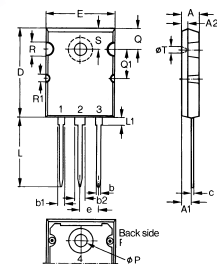
| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|--|---|------|------|
| | | min. | typ. | max. |
| g_{fs} | $V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ pulse test | 35 | 45 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 4600 | pF |
| C_{oss} | | | 1100 | pF |
| C_{rss} | | | 500 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2.0\ \Omega$ (External), | | 26 | ns |
| t_r | | | 50 | ns |
| $t_{d(off)}$ | | | 75 | ns |
| t_f | | | 20 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 180 | nC |
| Q_{gs} | | | 39 | nC |
| Q_{gd} | | | 100 | nC |
| R_{thJC} | | | 0.35 | K/W |
| R_{thCK} | TO-247 | | 0.25 | K/W |
| | TO-264 | | 0.15 | K/W |

TO-247 AD (IXFH) Outline



| Dim. | Millimeter | | Inches | |
|------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 19.81 | 20.32 | 0.780 | 0.800 |
| B | 20.80 | 21.46 | 0.819 | 0.845 |
| C | 15.75 | 16.26 | 0.610 | 0.640 |
| D | 3.55 | 3.65 | 0.140 | 0.144 |
| E | 4.32 | 5.49 | 0.170 | 0.216 |
| F | 5.4 | 6.2 | 0.212 | 0.244 |
| G | 1.65 | 2.13 | 0.065 | 0.084 |
| H | - | 4.5 | - | 0.177 |
| J | 1.0 | 1.4 | 0.040 | 0.055 |
| K | 10.8 | 11.0 | 0.426 | 0.433 |
| L | 4.7 | 5.3 | 0.185 | 0.209 |
| M | 0.4 | 0.8 | 0.016 | 0.031 |
| N | 1.5 | 2.49 | 0.087 | 0.102 |

TO-264 AA (IXFK) Outline

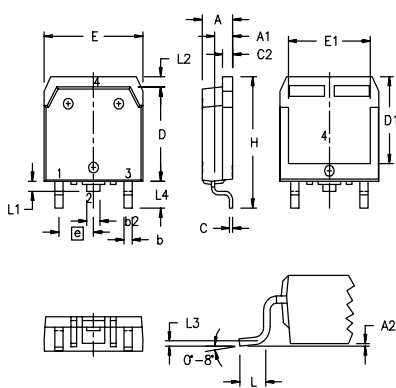


| Dim. | Millimeter | | Inches | |
|------|------------|-------|----------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.82 | 5.13 | .190 | .202 |
| A1 | 2.54 | 2.89 | .100 | .114 |
| A2 | 2.00 | 2.10 | .079 | .083 |
| b | 1.12 | 1.42 | .044 | .056 |
| b1 | 2.39 | 2.69 | .094 | .106 |
| b2 | 2.90 | 3.09 | .114 | .122 |
| c | 0.53 | 0.83 | .021 | .033 |
| D | 25.91 | 26.16 | 1.020 | 1.030 |
| E | 19.81 | 19.96 | .780 | .786 |
| e | 5.46 BSC | | .215 BSC | |
| J | 0.00 | 0.25 | .000 | .010 |
| K | 0.00 | 0.25 | .000 | .010 |
| L | 20.32 | 20.83 | .800 | .820 |
| L1 | 2.29 | 2.59 | .090 | .102 |
| P | 3.17 | 3.66 | .125 | .144 |
| Q | 6.07 | 6.27 | .239 | .247 |
| Q1 | 8.38 | 8.69 | .330 | .342 |
| R | 3.81 | 4.32 | .150 | .170 |
| R1 | 1.78 | 2.29 | .070 | .090 |
| S | 6.04 | 6.30 | .238 | .248 |
| T | 1.57 | 1.83 | .062 | .072 |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|---|---|------|---------------|
| | | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 80 A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | | | 320 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = I_S - di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ | | 1.2 | 200 ns |
| Q_{RM} | | | 10 | μC |
| I_{RM} | | | | A |

TO-268AA (D³ PAK)



| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|----------|------|
| | Min. | Max. | Min. | Max. |
| A | 4.9 | 5.1 | .193 | .201 |
| A1 | 2.7 | 2.9 | .106 | .114 |
| A2 | .02 | .25 | .001 | .010 |
| b | 1.15 | 1.45 | .045 | .057 |
| b ₂ | 1.9 | 2.1 | .75 | .83 |
| C | .4 | .65 | .016 | .026 |
| D | 13.80 | 14.00 | .543 | .551 |
| E | 15.85 | 16.05 | .624 | .632 |
| E ₁ | 13.3 | 13.6 | .524 | .535 |
| e | 5.45 BSC | | .215 BSC | |
| H | 18.70 | 19.10 | .736 | .752 |
| L | 2.40 | 2.70 | .094 | .106 |
| L1 | 1.20 | 1.40 | .047 | .055 |
| L2 | 1.00 | 1.15 | .039 | .045 |
| L3 | 0.25 BSC | | .010 BSC | |
| L4 | 3.80 | 4.10 | .150 | .161 |

Min. Recommended Footprint

